

GaAs Infrared Emitting Diodes

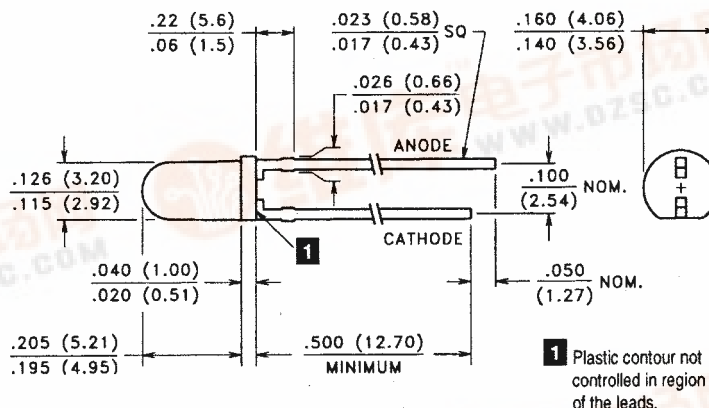
Long T-1 Plastic Package — 940 nm

捷多邦, 专业PCB打样工厂, 24小时加急出货

VTE3322LA, 24LA



PACKAGE DIMENSIONS inch (mm)



CASE 50A LONG T-1
CHIP SIZE: .011" X .011"

DESCRIPTION

This narrow beam angle, 3 mm diameter plastic packages, GaAs, 940 nm emitter is suitable for use in optical switch applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures		Maximum Reverse Current @ $V_R = 5V$:	10 μA
Storage and Operating:	-40°C to 100°C	Peak Wavelength (Typical):	940 nm
Continuous Power Dissipation:	100 mW	Junction Capacitance @ 0V, 1 MHz (Typ.):	14 pF
Derate above 30°C:	1.43 mW/°C	Response Time @ $I_F = 20 mA$	
Maximum Continuous Current:	50 mA	Rise: 1.0 μs Fall: 1.0 μs	
Derate above 30°C:	0.71 mA/°C	Lead Soldering Temperature:	260°C
Peak Forward Current, 10 μs , 100 pps:	3 A	(1.6 mm from case, 5 seconds max.)	
Temp. Coefficient of Power Output (Typ.):	-8%/°C		
Maximum Reverse Voltage:	5.0V		

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 123-124)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V _F		
	E _e		Condition		I _e	P _O	I _{FT}	@ I _{FT}		θ _{1/2}
	mW/cm ²		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE3322LA	1.0	1.3	10.16	2.1	1.0	1.5	20	1.25	1.6	±10°
VTE3324LA	2.0	2.6	10.16	2.1	2.0	2.5	20	1.25	1.6	±10°

Refer to General Product Notes, page 2.